

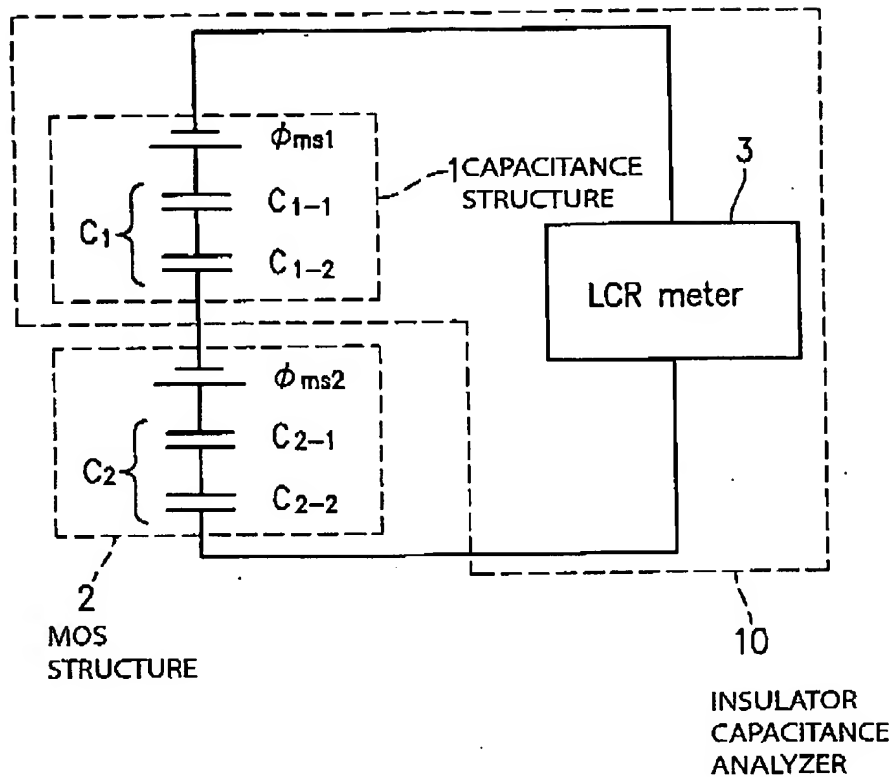
FIG. 1

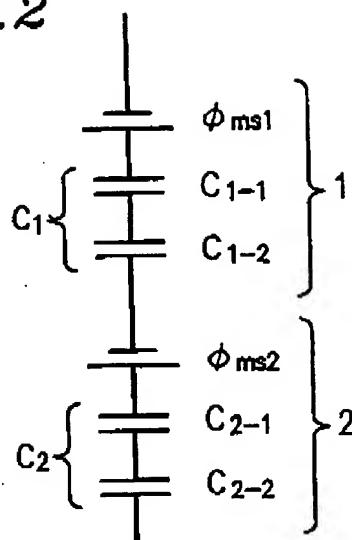
FIG. 2

FIG. 3

NMOS C-V Characteristics

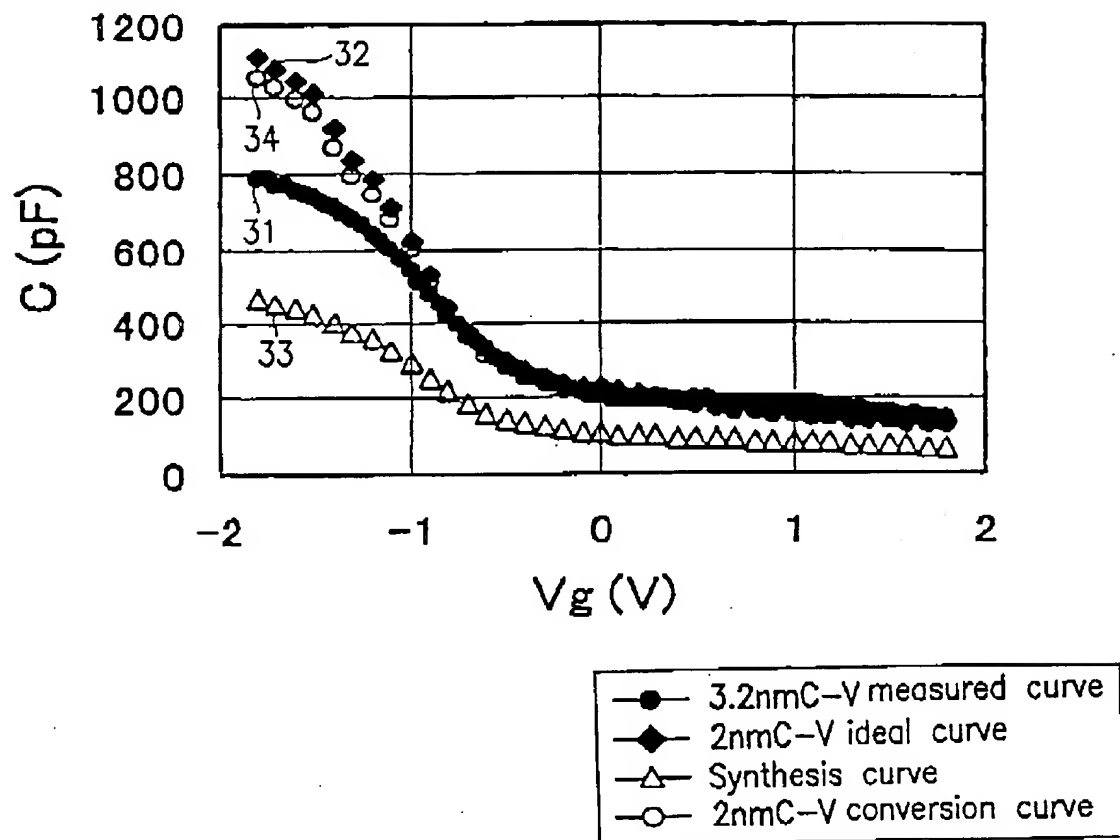


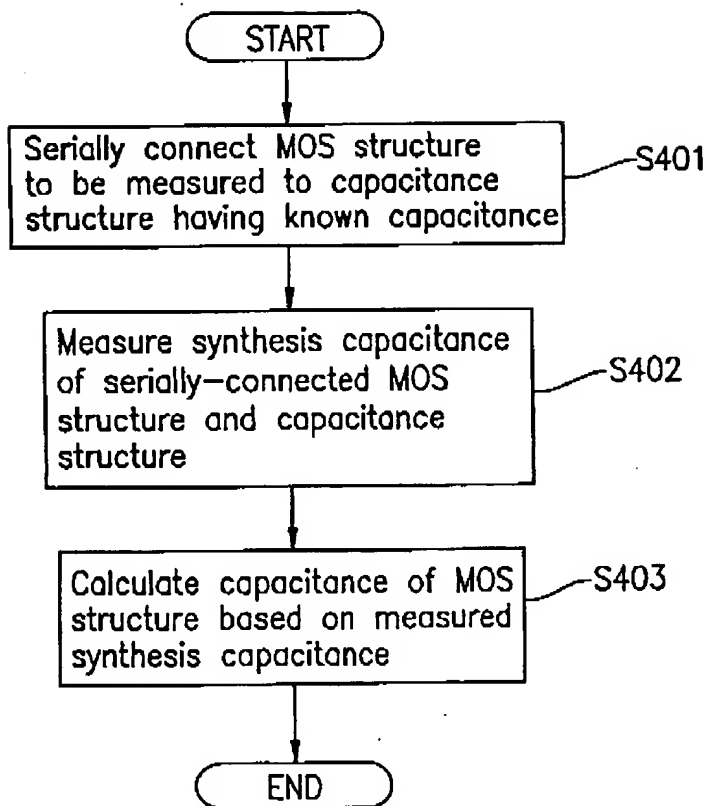
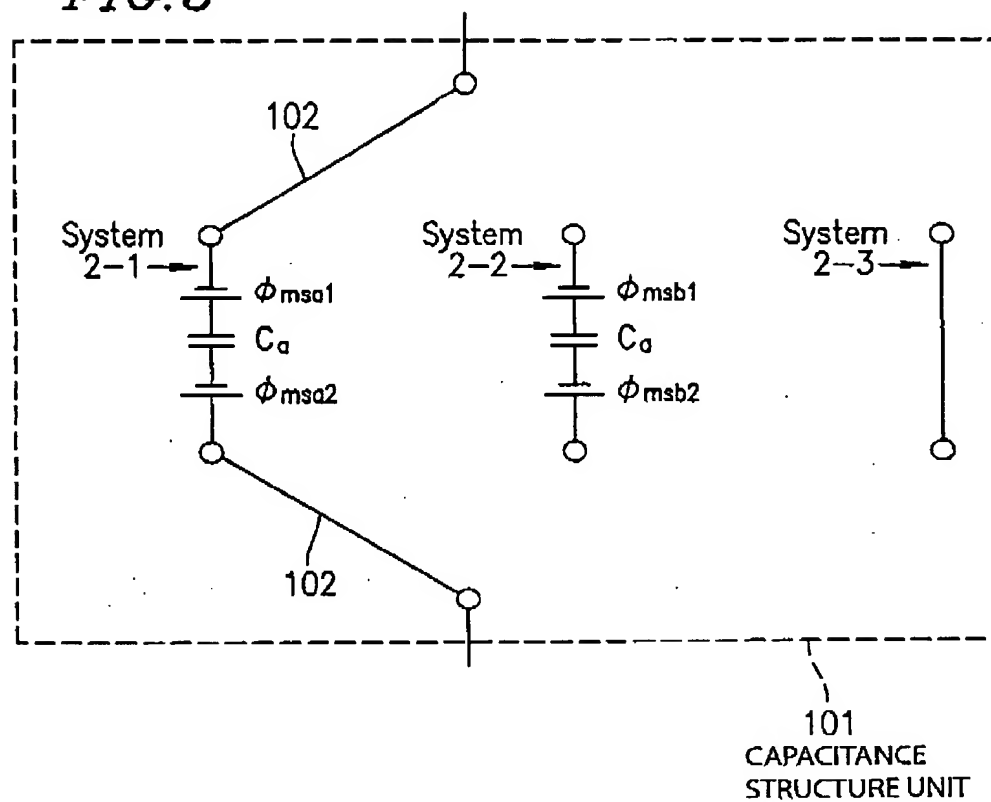
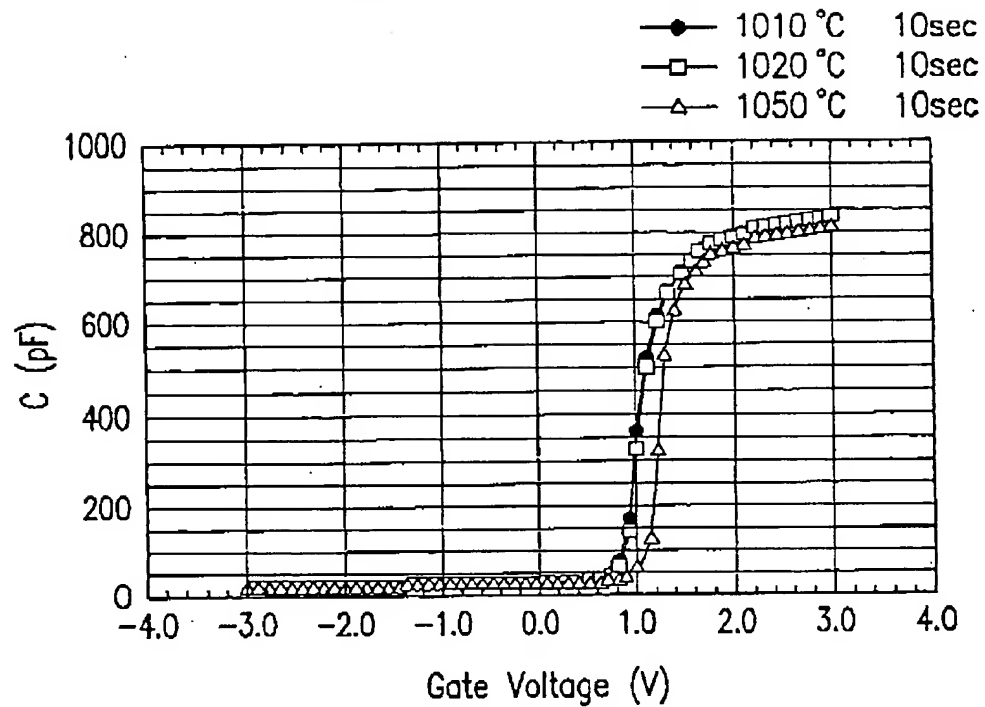
FIG. 4

FIG. 5

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FIG. 6

PMOS C-V Characteristics

Active Area: $9E-4\text{cm}^2$

w/o Well Imp.

Gate SiON: NO/N₂

poly Si: 200nm

P+Imp.: BF₂

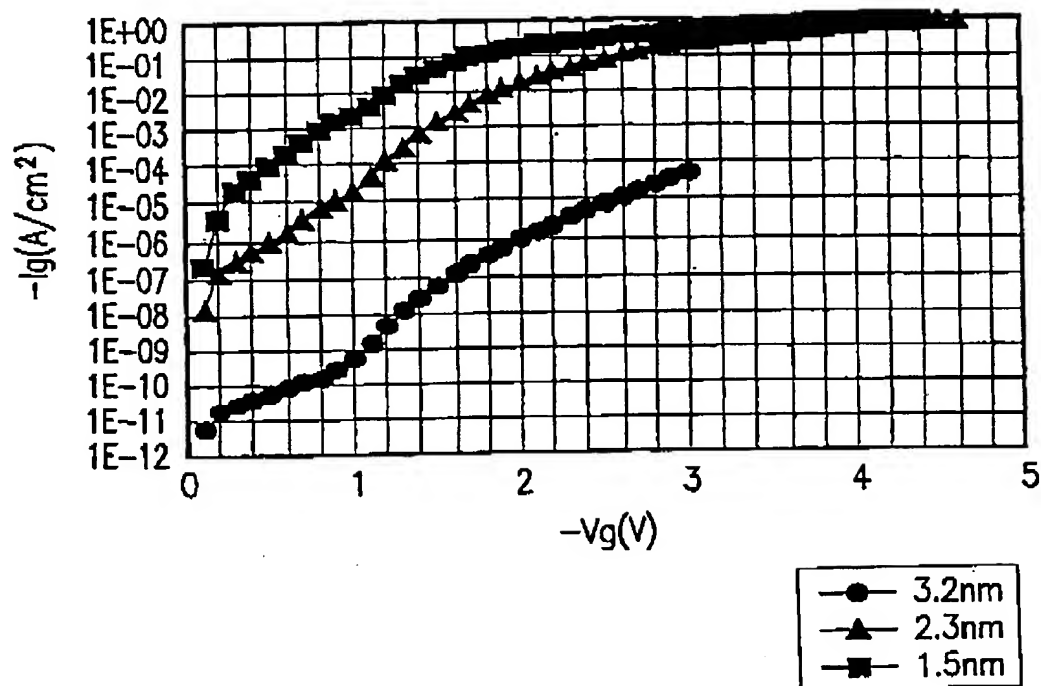
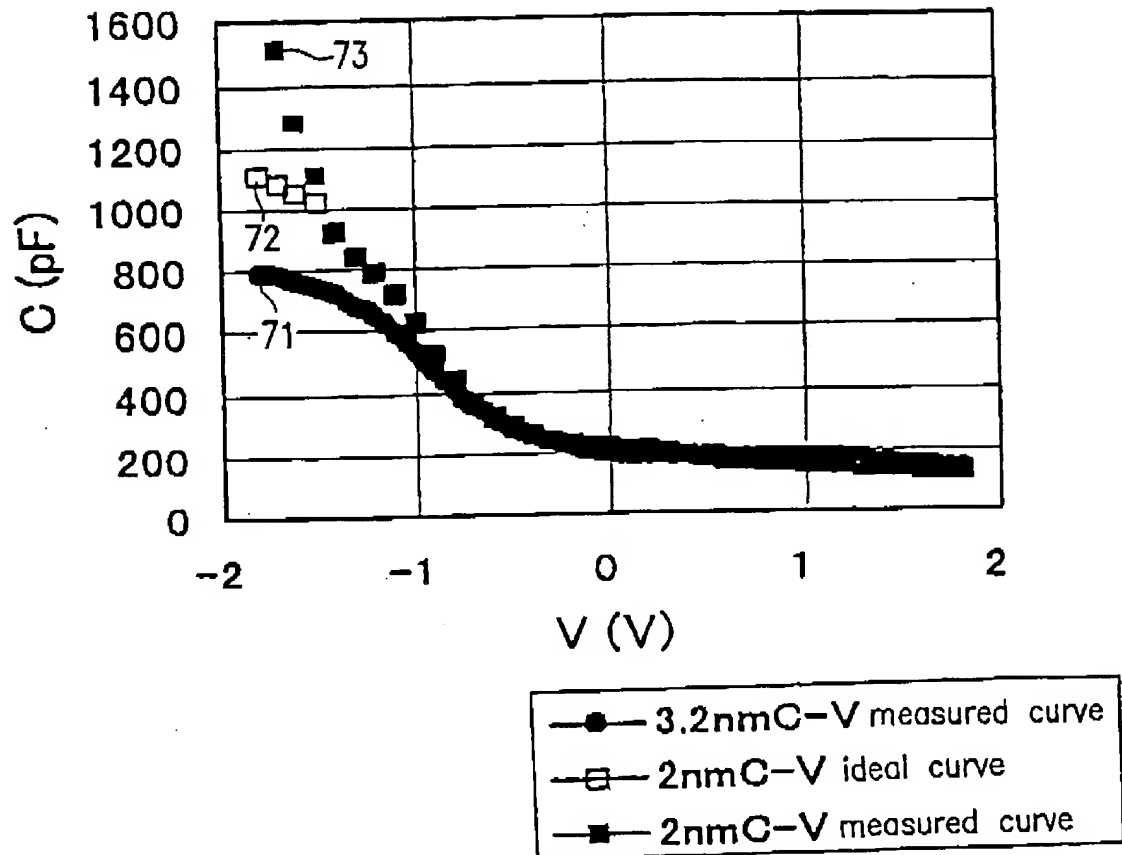
FIG. 7**NMOS I-V Characteristics**

FIG. 8 (PRIOR ART)
NMOS C-V Characteristics



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FIG. 9 (PRIOR ART)

